

RESISTIVE SWITCHING PHENOMENA IN NANOSCALE COMPLEX-OXIDE HETEROSTRUCTURES: RESPONSE TO THE AC SIGNAL

In order to identify a physical mechanism responsible for the resistive switching effect in memristive oxide-based structures, we propose to study an ac response to a periodic current or voltage perturbation. A minimalist model which accounts for the frequency impact on hysteresis phenomenon in current-voltage characteristics of the yttrium-barium-cuprate $\text{YBa}_2\text{Cu}_3\text{O}_{7-c}$ (YBCO) based contacts is proposed and analyzed numerically.

Primary authors: Dr ZHITLUKHINA, Elena (O.O. Galkin Donetsk Institute for Physics and Engineering, NASU); Dr PLECENIK, Tomas (Comenius University in Bratislava); BELOGOLOVSKII, Mikhail (G.V. Kurdyumov Institute for Metal Physics, National Academy of Sciences of Ukraine); Prof. KUS, Peter (Comenius University in Bratislava); Prof. PLECENIK, Andrej (Comenius University in Bratislava)

Presenter: Dr ZHITLUKHINA, Elena (O.O. Galkin Donetsk Institute for Physics and Engineering, NASU)

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